

# **DMP3098L**

#### P-Channel Enhancement Mode MOSFET

#### **Feature**

•-30V/-3.8A,  $R_{DS(ON)} = 55 m\Omega(MAX)$  @VGS = -10V.

 $R_{DS(ON)} = 70 m\Omega(MAX)$  @ $V_{GS} = -4.5V$ .

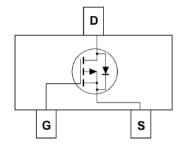
 $R_{DS(ON)}\!=\!120m\Omega(MAX)\ @V_{GS}\!=\!-2.5V.$ 

- •Super High dense cell design for extremely low RDS(ON)
- •Reliable and Rugged
- •SOT-23 for Surface Mount Package

#### **Applications**

- Power Management
- •Portable Equipment and Battery Powered Systems.





#### Absolute Maximum Ratings TA=25°C Unless Otherwise noted

Parameter	Symbol	Symbol Limit	
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	±12	V
Drain Current-Continuous	$I_D$	-3.8	A

#### Electrical Characteristics TA=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units	
Off Characteristics							
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=-250μA	-30	-	-	V	
Zero-Gate Voltage Drain Current	IDSS	VDS=-24V, VGS=0V	-	-	-1	μΑ	
Gate Body Leakage Current, Forward	IGSSF	VGS=12V, VDS=0V	-	-	100	nA	
Gate Body Leakage Current, Reverse	IGSSR	VGS=-12V, VDS=0V	-	-	-100	nA	
On Characteristics	•		•				
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=-250μA	-0.7	-	-1.3	V	
Static Drain-source On-Resistance RDS(	RDS(ON)	VGS =-10V, ID =-4.2A	-	50	55	$m\Omega$	
		VGS =-4.5V, ID =-4.0A	-	60	70	$m\Omega$	
		VGS =-2.5V, ID =-1.0A	-	80	120	$m\Omega$	
Drain-Source Diode Characteristics and Maximum Ratings							
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=-1.0A			-1.0	V	



## Typical Characteristics

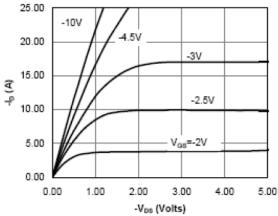


Fig 1: On-Region Characteristics

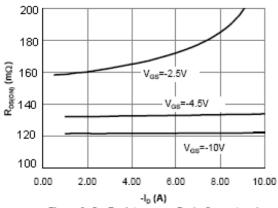


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

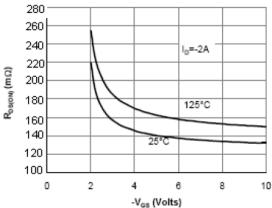


Figure 5: On-Resistance vs. Gate-Source Voltage

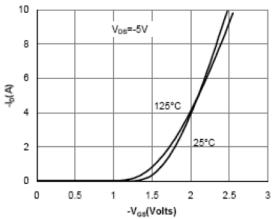
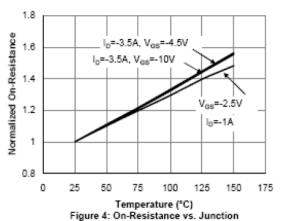


Figure 2: Transfer Characteristics



Temperature

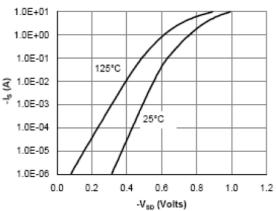
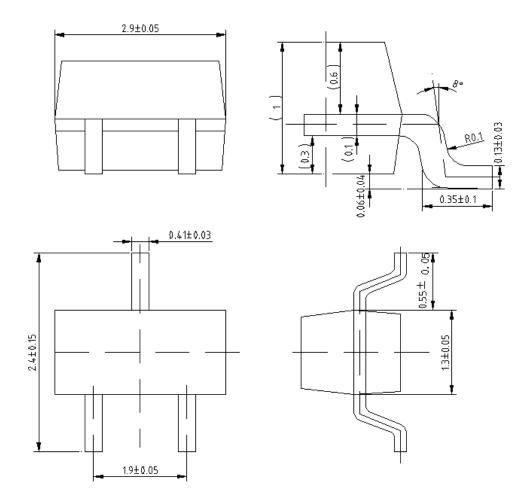


Figure 6: Body-Diode Characteristics



## Package Outline Dimensions (UNIT: mm)

SOT-23



### 单击下面可查看定价,库存,交付和生命周期等信息

>>SHIKUES(时科)